

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Original) A semiconductor device provided with high concentration source/drain layers of the reverse conductive type formed in a semiconductor layer of one conductive type, a gate electrode formed on a channel layer located between the source and drain layers, a body layer of one conductive type formed in the vicinity of the source layer and a low concentration drain layer of the reverse conductive type formed between the channel layer and the drain layer, wherein:

said body layer is formed only under said gate electrode.

2. (Original) A semiconductor device, according to claim 1, wherein the device comprises:

a gate electrode formed on a semiconductor layer of one conductive type via a gate oxide film;

a high concentration source layer of the reverse conductive type formed so that it is adjacent to one end of said gate electrode;

a high concentration drain layer of the reverse conductive type formed apart from the other end of said gate electrode;

a low concentration drain layer of the reverse conductive type extended from under said gate electrode and formed so that said low concentration drain layer of the reverse conductive type surrounds said drain layer of the reverse conductive type;

a body layer of one conductive type under said gate electrode formed between said source layer of the reverse conductive type and said drain layer of the reverse conductive type.

3. (Original) A semiconductor device, according to claim 1, wherein the device comprises:

a gate electrode formed on a semiconductor layer of one conductive type via a gate oxide film;

high concentration source/drain layers of the reverse conductive type formed apart from said gate electrode; and

low concentration source/drain layers of the reverse conductive type formed so that they respectively surround said source/drain layers of the reverse conductive type and parted by a body layer of one conductive type formed under said gate electrode.

4. (Original) A semiconductor device according to claim 1, wherein:

said low concentration drain layer of the reverse conductive type or said low concentration source/drain layers of the reverse conductive type are formed so that they are shallow under said gate electrode and are deep under said high concentration drain layer of the reverse conductive type or said high concentration source/drain layers of the reverse conductive type.

5. (Original) A semiconductor device, according to claim 1, wherein a reverse conductive type layer is formed in a surface portion of the body layer.

6-21. (Cancelled).